

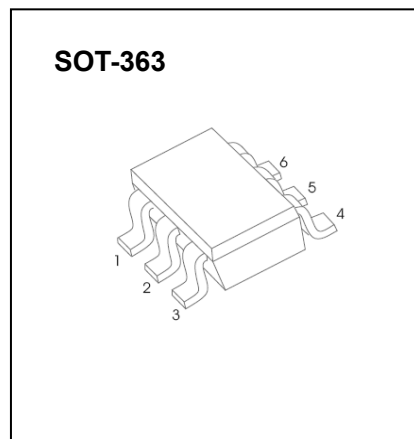
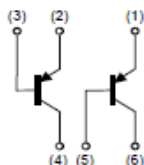
## SOT-363 Plastic-Encapsulate Transistors

**UMT2N** General purpose transistor (dual transistor)

**FEATURES**

Two 2SA1037AK chips in SOT-363 package

**MARKING: T2**



**Absolute maximum ratings (T<sub>a</sub>=25°C)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Collector Current	-150	mA
P <sub>C</sub>	Collector Power Dissipation	150	mW
R <sub>θJA</sub>	Thermal Resistance from Junction to Ambient	833	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

**Electrical Characteristics (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-50μA, I <sub>E</sub> =0	-60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-50μA, I <sub>C</sub> =0	-6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-60V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-6V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-1mA	120		560	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA			-0.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-12V, I <sub>C</sub> =-2mA, f=100MHz		140		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-12V, I <sub>E</sub> =0, f=1MHz			5	pF

